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May 2010

FDP8442_F085

N-Channel PowerTrench® MOSFET 40V, 80A, 3.1m Ω

Features

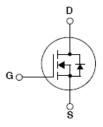
- Typ $r_{DS(on)} = 2.3m\Omega$ at $V_{GS} = 10V$, $I_D = 80A$
- Typ $Q_{g(10)} = 181nC$ at $V_{GS} = 10V$
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- Qualified to AEC Q101
- RoHS Compliant



Applications

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Electronic Steering
- Integrated Starter / Alternator
- Distributed Power Architectures and VRMs
- Primary Switch for 12V Systems





MOSFET Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	40	V
V_{GS}	Gate to Source Voltage	±20	V
	Drain Current Continuous (T _C <158°C, V _{GS} = 10V)	80	
I _D	Drain Current Continuous ($T_{amb} = 25^{\circ}C$, $V_{GS} = 10V$, with $R_{\theta,JA} = 62^{\circ}C/W$)	23	Α
	Pulsed	See Figure 4	
E _{AS}	Single Pulse Avalanche Energy (Note 1)	720	mJ
D	Power Dissipation	254	W
P_D	Derate above 25°C	1.7	W/°C
T_J , T_{STG}	Operating and Storage Temperature	-55 to +175	°C

Thermal Characteristics

$R_{\theta,JC}$	Thermal Resistance Junction to Case	0.59	°C/W	
R _{e.IA}	Thermal Resistance Junction to Ambient	(Note 2)	62	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP8442	FDP8442_F085	TO-220AB	Tube	N/A	50 units

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

Parameter

Gate to Source Leakage Current

Off Ch	Off Characteristics						
B _{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	40	-	-	V	
	Zana Oala Vallana Busin Oanad	V _{DS} = 32V	-	-	1		
I _{DSS} Zero	Zero Gate Voltage Drain Current	V _{GS} = 0V T ₁ = 150°C	_	_	250	μΑ	

 $V_{GS} = \pm 20V$

Test Conditions

Min

Тур

Max

Units

On Characteristics

Symbol

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	2.9	4	V
	$I_D = 80A, V_{GS} = 10V$	-	2.3	3.1		
r _{DS(on)}	Drain to Source On Resistance	$I_D = 80A, V_{GS} = 10V,$ $T_1 = 175^{\circ}C$	-	3.9	5.3	mΩ

Dynamic Characteristics

C _{iss}	Input Capacitance	.,	-	12200	-	pF
Coss	Output Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	-	1040	-	pF
C _{rss}	Reverse Transfer Capacitance	I = IIVINZ	-	640	-	pF
R_{G}	Gate Resistance	$V_{GS} = 0.5V, f = 1MHz$	-	1.0	-	Ω
$Q_{g(TOT)}$	Total Gate Charge at 10V	V _{GS} = 0 to 10V	-	181	235	nC
Q _{g(TH)}	Threshold Gate Charge	$V_{GS} = 0 \text{ to } 2V$ $V_{DD} = 2$	ov -	23	30	nC
Qgs	Gate to Source Gate Charge	I _D = 80A		49	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau	$I_g = 1mA$	٠_	26	-	nC
Q _{ad}	Gate to Drain "Miller" Charge		-	41	-	nC

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Switchi	ng Characteristics					
t _(on)	Turn-On Time		-	-	62	ns
t _{d(on)}	Turn-On Delay Time		-	19.5	-	ns
t _r	Turn-On Rise Time	$V_{DD} = 20V, I_{D} = 80A$	-	19.3	-	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10V, R_{GS} = 2\Omega$	-	57	-	ns
t _f	Turn-Off Fall Time		-	17.2	-	ns
t _{off}	Turn-Off Time		-	-	118	ns

Drain-Source Diode Characteristics

V _{SD} Source to Drain Diode Voltage	On the David Breath Welliam	I _{SD} = 80A	ı	0.9	1.25	V
	Source to Drain Diode Voltage	I _{SD} = 40A	-	0.8	1.0	V
t _{rr}	Reverse Recovery Time	I _F = 75A, di/dt = 100A/μs	1	49	64	ns
Q_{rr}	Reverse Recovery Charge	I _F = 75A, di/dt = 100A/μs	-	70	91	nC

Starting T_J = 25°C, L = 0.35mH, I_{AS} = 64A
 Pulse width = 100s.

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: http://www.aecouncil.com/
All Fairchild Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

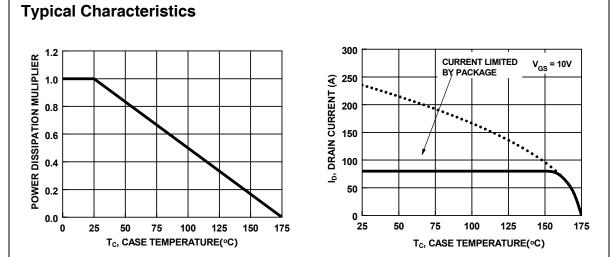


Figure 1. Normalized Power Dissipation vs Case Temperature

Figure 2. Maximum Continuous Drain Current vs
Case Temperature

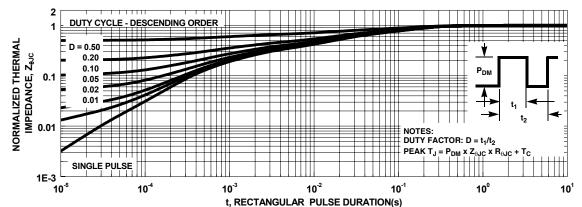


Figure 3. Normalized Maximum Transient Thermal Impedance

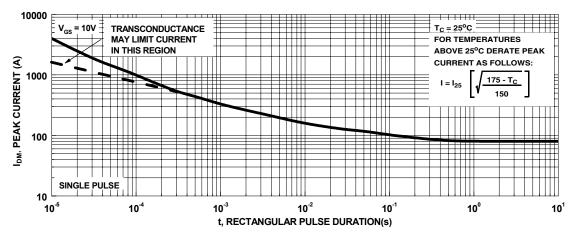


Figure 4. Peak Current Capability

Typical Characteristics

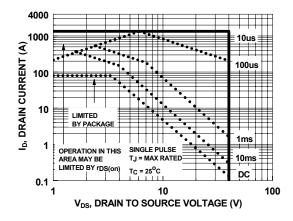
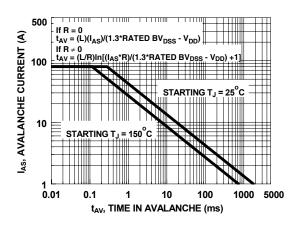


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching

Capability

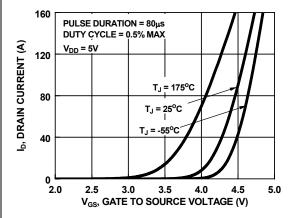


Figure 7. Transfer Characteristics

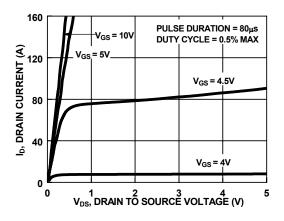


Figure 8. Saturation Characteristics

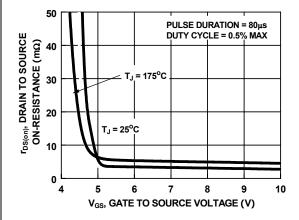


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

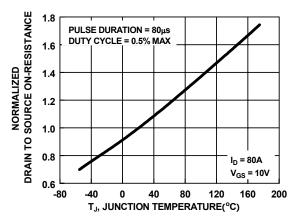


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics

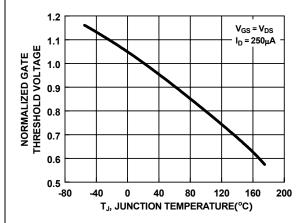


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

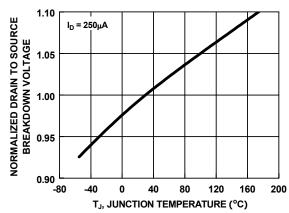


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

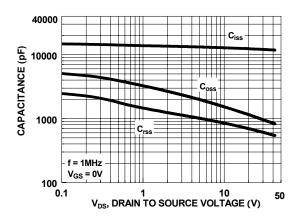


Figure 13. Capacitance vs Drain to Source Voltage

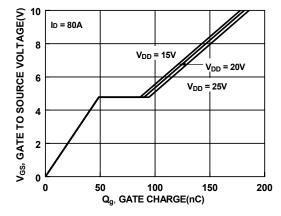


Figure 14. Gate Charge vs Gate to Source Voltage





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